

Features

- Trench Power LV MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low RDS(ON)
- Moisture Sensitivity Level 3
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

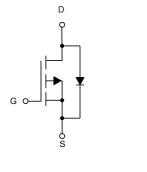
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 50°C/W Junction to Ambient(Note2)
- Thermal Resistance: 1.5°C/W Junction to Case

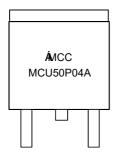
Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	-40	V	
Gate-Source Volltage		V _{GS}	±20	V	
Continuous Drain Current	T _C =25°C		-50	А	
	T _C =100°C	- I _D	-31		
Pulsed Drain Current ^(Note3)		I _{DM}	-200	Α	
Total Power Dissipation ^(Note4)		P _D	83	W	
Single Pulsed Avalanche Energy ^(Note5)		E _{AS}	100	mJ	

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta,JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. $\ensuremath{P_{D}}$ is based on max. junction temperature, using junction-case thermal resistance.
- 5. V_{DD} =-30V, V_{GS} = -10V, L= 0.5mH

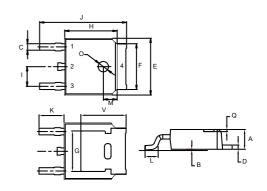
Internal Structure and Marking Code





P-CHANNEL MOSFET

DPAK(TO-252)



- Gate
- 2,4. Drain
 - 3. Source

	DIMENSIONS					
DIM	INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE	
Α	0.087	0.094	2.20	2.40		
В	0.000	0.005	0.00	0.13		
С	0.026	0.034	0.66	0.86		
D	0.018	0.023	0.46	0.58		
Е	0.256	0.264	6.50	6.70		
F	0.201	0.215	5.10	5.46		
G	0.190		4.83		TYP.	
Н	0.236	0.244	6.00	6.20		
I	0.086	0.094	2.18	2.39		
J	0.386	0.409	9.80	10.40		
K	0.114		2.90		TYP.	
L	0.055	0.067	1.40	1.70		
M	0.063		1.60		TYP.	
0	0.043	0.051	1.10	1.30		
Q	0.000	0.012	0.00	0.30		
V	0.211		5.35		TYP.	

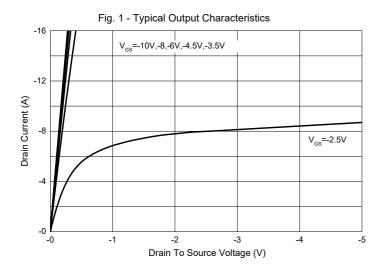


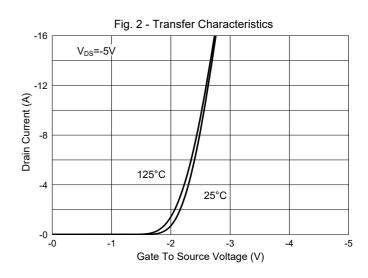
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

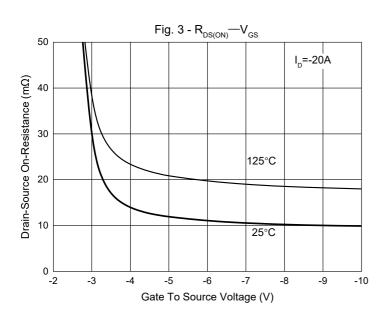
Drain-Source Breakdown Voltage V _{(BR)DSS} V _{GS} =0V, I _D =-250μA -40 V NA	Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Searce Courtee Cour	Static Characteristics			'		1		
Zero Gate Voltage Drain Current I_{DSS} $V_{DS}=-40V$, $V_{GS}=0V$ -1 μA Gate-Threshold Voltage $V_{OS}(m)$ $V_{DS}=V_{OS}$, $I_D=-250\mu A$ -1.0-1.4-2.5 V Drain-Source On-Resistance $R_{DS}(m)$ $V_{OS}=-10V$, $I_D=-20A$ 1015 $m\Omega$ Gate Resistance R_g $F=1$ MHz, Open drain9 Ω Diode CharacteristicsContinuous Body Diode Current I_S $I_S=-20A$ -1.2 V Diode Forward Voltage V_{SD} $V_{OS}=0V$, $I_S=-20A$ -1.2 V Reverse Recovery Time I_T $I_T=-4A$, $I_T=-4A$	Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-40			V	
	Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Drain-Source On-Resistance $R_{DS(on)}$ $V_{GS}=-10V$, $I_D=-20A$ 10 15 $m\Omega$ Gate Resistance R _g F=1 MHz, Open drain 9 Ω Diode Characteristics Continuous Body Diode Current I _s -50 A Diode Forward Voltage V _{SD} V _{GS} =0V, I _S =-20A -1.2 V Reverse Recovery Time t _r I _F =-4A, dI _F /dt=100A/μs 51 ns Reverse Recovery Charge Q _{rr} 41 nC Dynamic Characteristics Input Capacitance C _{iss} V _{DS} =-30V,V _{GS} =0V,f=1MHz 224 pF Reverse Transfer Capacitance C _{rss} 198 198 198 Total Gate Charge Q _g 75 8 nC Gate-Source Charge Q _g 15 15 15 Turn-On Delay Time t _d V _{DD} =-20V, V _{GS} =-10V, R _{GEN} =20V, V _{GS} =-10V, R _{GEN} =3Ω, I _{DS} =-4A 200 15	Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V			-1	μA	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1.0	-1.4	-2.5	V	
V _{GS} =-4.5V, I _D =-15A 12 20	Drain Course On Registeres	Regul	V_{GS} =-10V, I_{D} =-20A		10 15		mΩ	
Diode Characteristics Continuous Body Diode Current I _S -50 A Diode Forward Voltage V _{SD} V _{GS} =0V, I _S =-20A -1.2 V Reverse Recovery Time t _{rr} I _F =-4A, dI _F /dt=100A/μs 51 ns Reverse Recovery Charge Q _{rr} 41 nC Dynamic Characteristics Input Capacitance C _{Iss} 3302 P Output Capacitance C _{rss} 198 P Reverse Transfer Capacitance C _{rss} 198 P Total Gate Charge Q _g 75 P Gate-Source Charge Q _g 75 P Gate-Source Charge Q _{gd} 15 T Turn-On Delay Time t _r V _{DD} =-20V, V _{GS} =-10V,	Drain-Source On-Resistance	DS(on)	V_{GS} =-4.5V, I_{D} =-15A		12	20	11122	
Continuous Body Diode Current I_S V_{SD} $V_{GS}=0V, I_S=-20A$ -1.2 V Reverse Recovery Time t_{rr} $I_F=-4A, dI_F/dt=100A/\mu s$ -1.2 V -1.2 V Reverse Recovery Charge $I_F=-4A, dI_F/dt=100A/\mu s$ -1.2 V -1.2 -1.2 V	Gate Resistance	R_g	F=1 MHz, Open drain		9		Ω	
Diode Forward Voltage V_{SD} $V_{GS}=0V$, $I_S=-20A$ -1.2 V Reverse Recovery Time t_{rr} Reverse Recovery Charge Q_{rr} $I_F=-4A$, $dI_F/dt=100A/\mu s$ -1.2 V $-1.$	Diode Characteristics							
Reverse Recovery Time t_{rr}	Continuous Body Diode Current	Is				-50	Α	
Reverse Recovery Charge Q_{rr} $I_F=-4A$, $dI_F/dt=100A/\mu s$ 41 nC Dynamic Characteristics Input Capacitance C_{iss} $V_{DS}=-30V, V_{GS}=0V, f=1MHz$ 224 pF Reverse Transfer Capacitance Q_g Total Gate Charge Q_g $V_{DS}=-20V, V_{GS}=-10V, I_D=-4A$ 8 nC Gate-Drain Charge Q_{gd}	Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-20A			-1.2	V	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Reverse Recovery Time	t _{rr}	I = 4A dI /dt=100A/us		51		ns	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Reverse Recovery Charge	Q _{rr}	1=-4Λ, αιε/αι-100Λ/μ5		41		nC	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Dynamic Characteristics							
Reverse Transfer Capacitance C_{rss} 198 Total Gate Charge Q_g 75 Gate-Source Charge Q_{gs} V_{DS} =-20V, V_{GS} =-10V, I_D =-4A 8 nC Gate-Drain Charge Q_{gd} 15 Turn-On Delay Time $t_{d(on)}$ 7.5 Turn-On Rise Time t_r V_{DD} =-20V, V_{GS} =-10V, V_{DS} =	Input Capacitance	C _{iss}			3302			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Output Capacitance	C _{oss}	V_{DS} =-30V, V_{GS} =0V,f=1MHz		224		pF	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Reverse Transfer Capacitance	C _{rss}			198			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Total Gate Charge	Qg			75			
	Gate-Source Charge	Q _{gs}	V_{DS} =-20V, V_{GS} =-10V, I_{D} =-4A		8		nC	
Turn-On Rise Time t_r V_{DD} =-20V, V_{GS} =-10V, $t_{d(off)}$ V_{DD} =-24A $t_{d(off)}$	Gate-Drain Charge	Q_{gd}			15			
Turn-Off Delay Time $t_{d(off)}$ $R_{GEN}=3\Omega, I_{DS}=-4A$ 200	Turn-On Delay Time	t _{d(on)}			7.5			
Turn-Off Delay Time $t_{d(off)}$ $R_{GEN}=3\Omega, I_{DS}=-4A$ 200	Turn-On Rise Time	t _r	V _{DD} =-20V, V _{GS} =-10V,		4.2		,	
Turn-Off Fall Time t _f 70	Turn-Off Delay Time	t _{d(off)}	$R_{GEN}=3\Omega$, $I_{DS}=-4A$		200		1115	
	Turn-Off Fall Time	t _f			70			

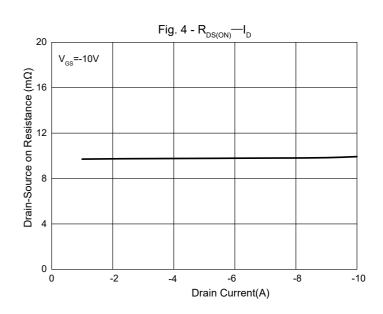


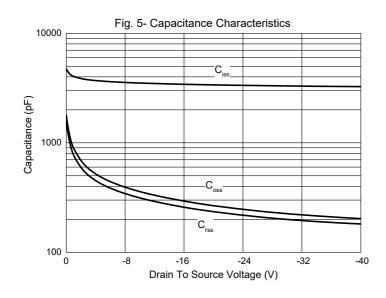
Curve Characteristics

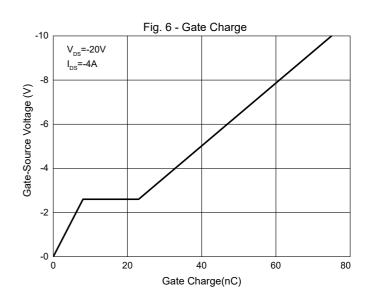






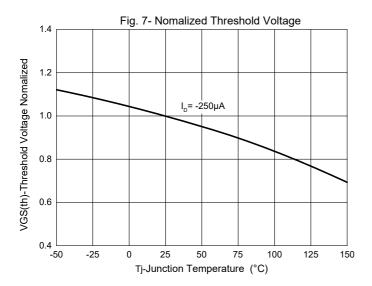


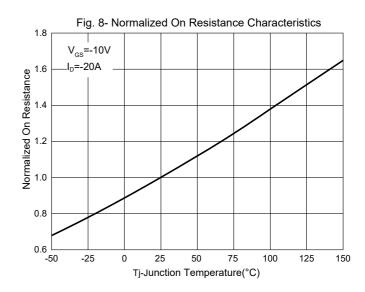


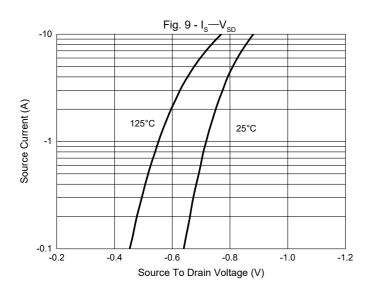


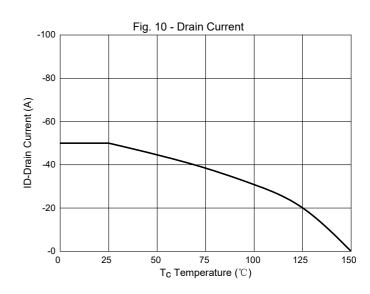


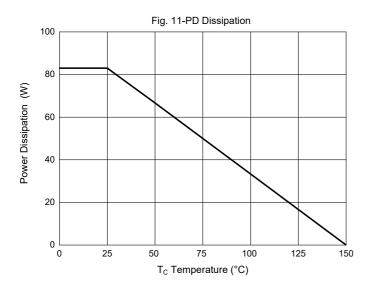
Curve Characteristics





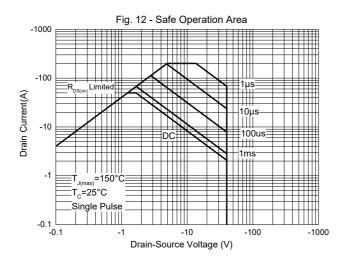


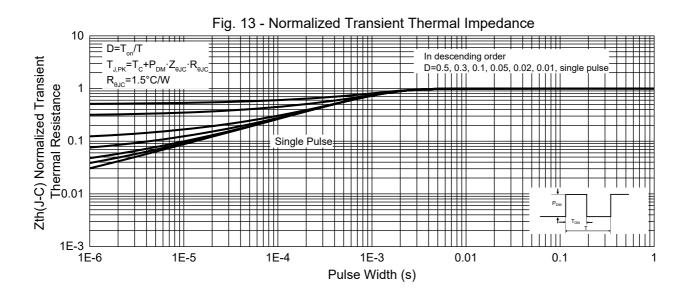






Curve Characteristics







Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel	

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